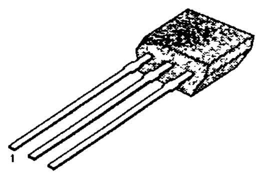
KSC2710 NPN EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER

- **Complement to KSA1150**
- **Collector Dissipation P_C=300mW**

TO-92S



1. Emitter 2. Collector 3. Base

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	500	mA
Collector Dissipation	P_C	300	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	−55 ~ 150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=100μA, I_E=0	40			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=10mA, I_B=0	20			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=−100μA, I_C=0	5			V
Collector Cut-off Current	I_{CBO}	V_{CB}=25V, I_E=0			0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=3V, I_C=0			0.1	μA
DC Current Gain	h_{FE}	V_{CE}=1V, I_C=0.1A	40		400	
Collector-Emitter Saturation Voltage	V_{CE} (sat)	I_C=0.5A, I_B=0.05A		0.18	0.4	V

h_{FE} CLASSIFICATION

Classification	R	O	Y	G
h_{FE}	40-80	70-140	120-240	200-400

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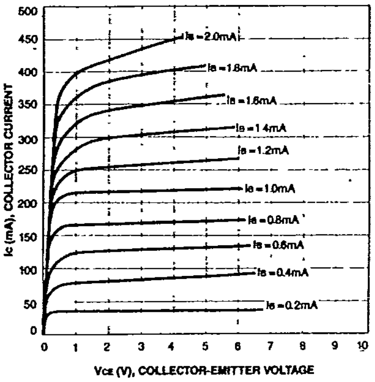
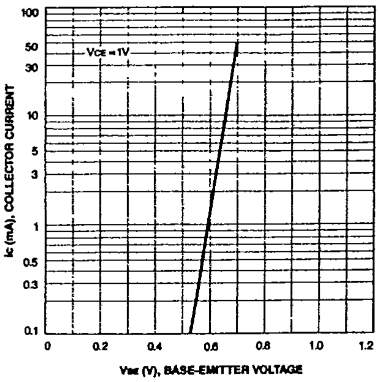
T-29-17

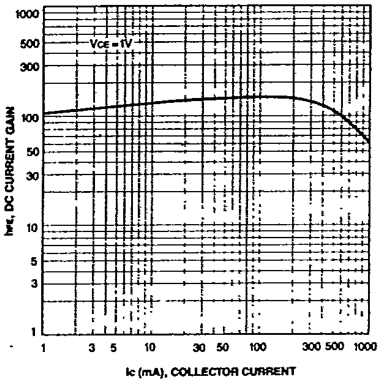
STATIC CHARACTERISTIC



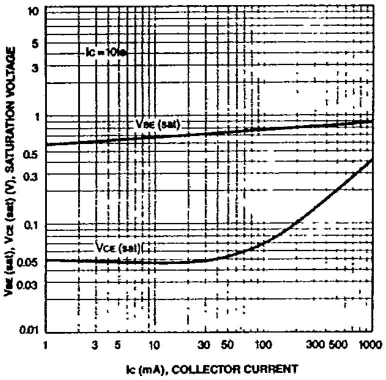
BASE-EMITTER ON VOLTAGE



DC CURRENT GAIN



BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



COLLECTOR OUTPUT CAPACITANCE